

Standard specifications of 100 mm β -Ga₂O₃ epitaxial wafer (by HVPE)

Epitaxial layer

Items	Specifications
Dopant	Si+Cl ^{*1} (n-type)
Doping concentration	$1 \times 10^{16} \text{ cm}^{-3}$
Thickness <small>*A value can be selected in increments 1 μm.</small>	5–10 μm

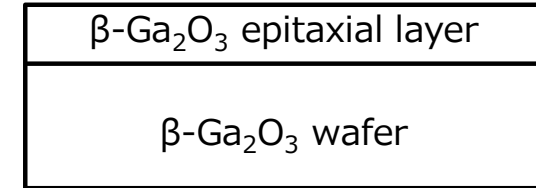
*1: Unintentionally-doped

Epi-Wafer

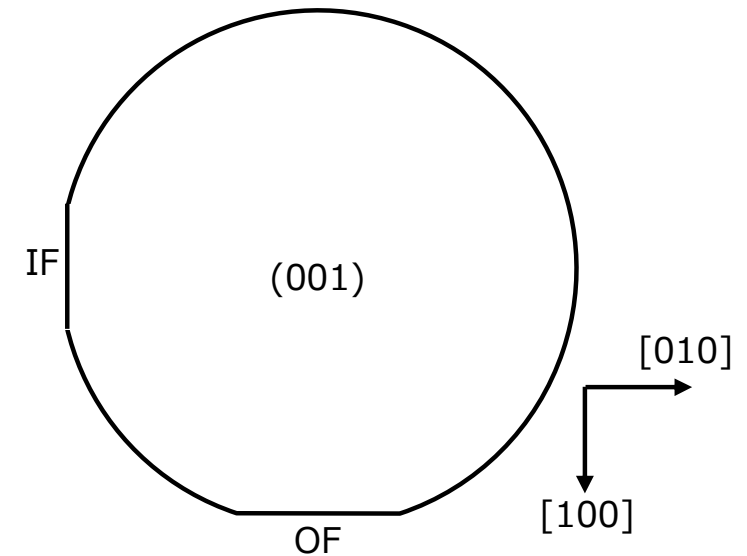
Items	Specifications
Substrate dopant	Sn (n-type)
Substrate resistivity	0.007–0.042 $\Omega \cdot \text{cm}$
Surface orientation	(001)
Backside finish	CMP
Wafer thickness	650 μm
XRD FWHM <small>*Not included in a delivery inspection sheet</small>	$\leq 50 \text{ arcsec}$

Remarks

- 1 There are cases in which the other side of OF is chipped (a maximum of around IF width).
- 2 These products must be used for research and development purposes only.
- 3 The substrates must not be used as a seed crystal.
- 4 The specifications are subject to change without notice.



Cross section of β -Ga₂O₃ epitaxial wafer



Orientation



Standard specifications of 2 inch β -Ga₂O₃ epitaxial wafer (by HVPE)

Epitaxial layer

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Dopant	Si+Cl ^{*1} (n-type)
Doping concentration	$1 \times 10^{16} \text{ cm}^{-3}$
Thickness <small>*A value can be selected in increments 1 μm.</small>	5–10 μm

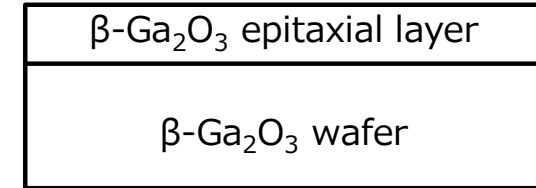
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Epi-Wafer

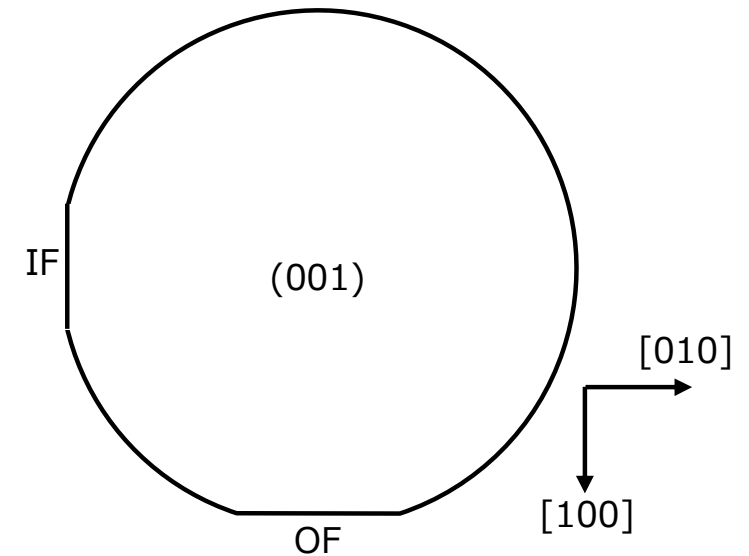
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Cross section of β -Ga₂O₃ epitaxial wafer



Orientation

